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Renesas Technology Corp.
Customer Support Dept.
April 1, 2003

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Keep safety first in your circuit designs!

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Remember to give due consideration to safety when making your circuit designs, with appropriate measures such as (i) placement of substitutive, auxiliary circuits, (ii) use of nonflammable material or (iii) prevention against any malfunction or mishap.

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HSM88WK

Silicon Schottky Barrier Diode for Balanced Mixer



ADE-208-049F (Z)

Rev. 6
Jul. 1998

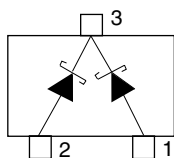
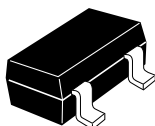
Features

- Proof against high voltage.
- MPAK package is suitable for high density surface mounting and high speed assembly.

Ordering Information

Type No.	Laser Mark	Package Code
HSM88WK	C4	MPAK

Pin Arrangement



(Top View)

- 1 Anode
- 2 Anode
- 3 Cathode

HSM88WK

Absolute Maximum Ratings

(T_a = 25°C)

Item	Symbol	Value	Unit
Reverse voltage	V _R	10	V
Average rectified current	I _O ^{*1}	15	mA
Junction temperature	T _j	125	°C
Storage temperature	T _{stg}	–55 to +125	°C

Notes 1. Per one device

Electrical Characteristics^{*1}

(T_a = 25°C)

Item	Symbol	Min	Typ	Max	Unit	Test Condition
Forward voltage	V _{F1}	350	—	420	mV	I _F = 1 mA
	V _{F2}	500	—	580		I _F = 10 mA
Reverse current	I _{R1}	—	—	0.2	μA	V _R = 2V
	I _{R2}	—	—	10		V _R = 10V
Capacitance	C	—	—	0.85	pF	V _R = 0V, f = 1 MHz
Capacitance deviation	ΔC	—	—	0.10	pF	V _R = 0V, f = 1 MHz
Forward voltage deviation	ΔV _F	—	—	10	mV	I _F = 10 mA
ESD-Capability ^{*2}	—	30	—	—	V	C=200pF , Both forward and reverse direction 1 pulse.

Notes 1. Per one device

Notes 2. Failure criterion ; I_R ≥ 400nA at V_R = 2 V

Main Characteristic

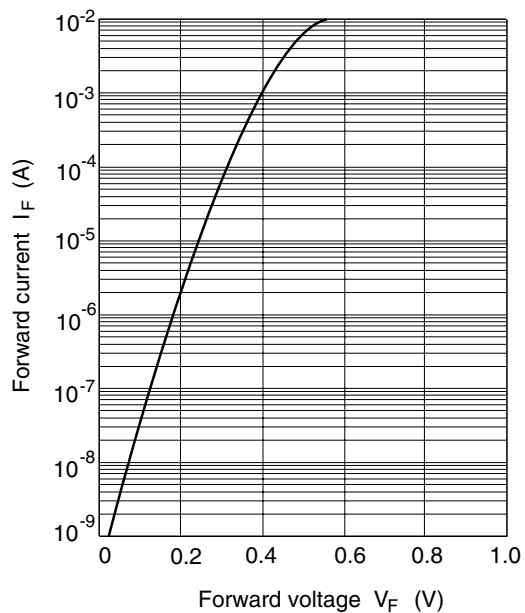


Fig.1 Forward current Vs. Forward voltage

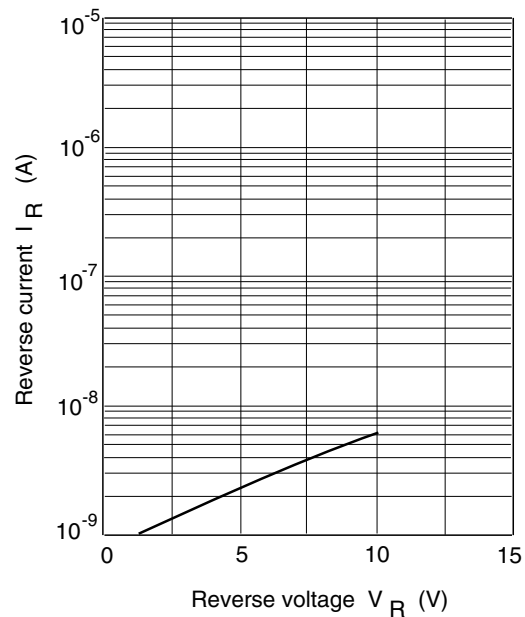


Fig.2 Reverse current Vs. Reverse voltage

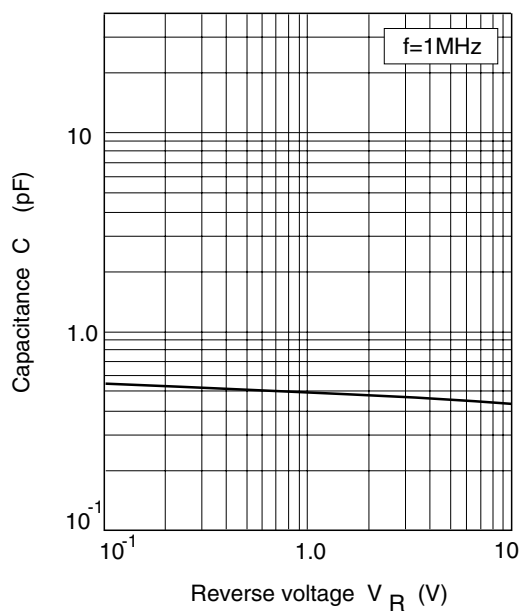
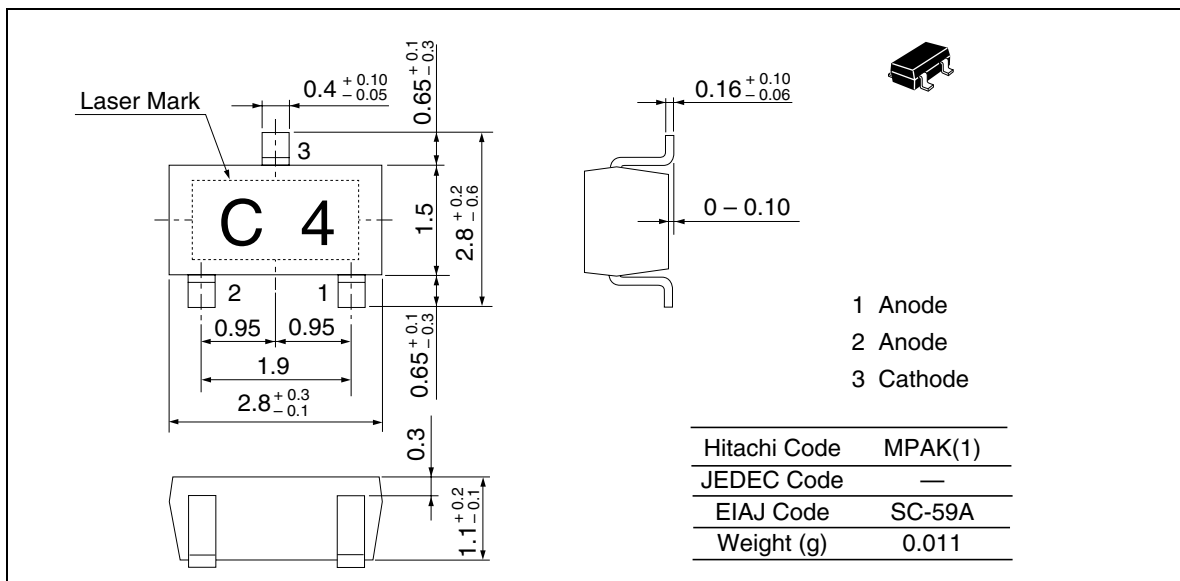


Fig.3 Capacitance Vs. Reverse voltage

HSM88WK

Package Dimensions

Unit : mm



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